1	L Number	Hits	Search Text	DB	Time stamp
Wafer or semiconductor() and (((cleaning ADD)5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) with microwave) or (heating ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or (removing adj residue) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADD5 (WAFER OR SEMICONDUCTOR OR CHIP)) adj5 microwave		59	(plasma and etching and heating and	IISDAT:	2004/08/20
OR SEMICONDUCTOR OR CHIP) with microwave) 1	-		(wafer or semiconductor)) and ((((cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or	US-PGPUB; EPO; JPO;	
1	2	7	OR SEMICONDUCTOR OR CHIP))) with microwave) or (heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave)) (heating with microwave) with plasma	-	
OR CHIP) or ((removing adj residue) ADJ5 US-PGPUB; EPG, JPO; Core semiconductor)			adj chamber	EPO; JPO;	10.33
20986 plasma and etching and heating and (wafer USPAT; US-PGPUB; EPO; JPO; IBM TDB USPAT; US-PGPUB; USPAT; US-PG	3	47	OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))) with	US-PGPUB; EPO; JPO;	
1663 wafer and boat and (batch or plurality adj4 wafers) USPĀT; US-PGPUB; EPO; JPO; IBM TDB USPĀT; US-PGPUB; USPĀT; US-PGPUB; US-PGPU	-	20986	plasma and etching and heating and (wafer	US-PGPUB; EPO; JPO;	1
16986 microwave with heating		1663		USPAT; US-PGPUB; EPO; JPO;	
-	~	16986	microwave with heating	USPAT; US-PGPUB; EPO; JPO;	1
- 0 oscillat\$ and polar adj molocules SPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; IBM_TDB U		441	(wafer or semiconductor)) and (microwave	USPAT; US-PGPUB; EPO; JPO;	
- 0 polar adj molocules	-	. 0	oscillat\$ and polar adj molocules	USPAT; US-PGPUB; EPO; JPO;	1
1621 dipoles and oscill\$ USPĀT; US-PGPUB; 13:03	-	0	polar adj molocules	USPAT; US-PGPUB; EPO; JPO;	1
- 463 microwave\$ and (dipoles and oscill\$) - 0 (wafer and boat and (batch or plurality adj4 wafers)) and (microwave\$ and (dipoles and oscill\$)) - 8 (plasma and etching and heating and (wafer or semiconductor)) and (microwave\$ uspAT; 2004/08/17 uspGPUB; EPO; JPO; IBM TDB uspAT; 2004/08/17 uspAT; 20		1621	dipoles and oscill\$	USPAT; US-PGPUB; EPO; JPO;	1
- 0 (wafer and boat and (batch or plurality adj4 wafers)) and (microwave\$ and (dipoles and oscill\$)) - 8 (plasma and etching and heating and (wafer or semiconductor)) and (microwave\$ uspAT; 2004/08/17 uspAT; 2	-	463	microwave\$ and (dipoles and oscill\$)	USPAT; US-PGPUB; EPO; JPO;	1
- 2865 DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) 3 (DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) 3 (DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) adj5 microwave 4 (plasma and etching and heating and (wicrowave) USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; USPAT; USPAT; USPAT; IBM_TDB USPAT; USPA	-	0	adj4 wafers)) and (microwave\$ and	USPAT; US-PGPUB; EPO; JPO;	1
- 2865 DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) 3 (DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) adj5 microwave USPĀT; 2004/08/17 US-PGPUB; 13:49 USPĀT; 2004/08/17 USPĀT; 2004/08/17 USPĀT; 13:30	_	8	(wafer or semiconductor)) and (microwave\$	USPĀT; US-PGPUB; EPO; JPO;	l l
- 3 (DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR USPAT; 2004/08/17 CHIP)) adj5 microwave US-PGPUB; 13:30	-	2865		USPĀT; US-PGPUB; EPO; JPO;	
IBM TDB		3		USPĀT; US-PGPUB; EPO; JPO;	I I

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-	6	(DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) with microwave	USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:30
_	4	(DRYING ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) adj7 microwave	IBM_TDB USPAT; US-PGPUB;	2004/08/17
			EPO; JPO; IBM_TDB	
_	9756	cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17
_	74	(removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	USPAT; US-PGPUB; EPO; JPO;	2004/08/17 13:48
-	175	(removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:48
-	9843	(cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 13:48
-	14985	heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:49
-	108	heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:50
-	152	(((cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))) with microwave) or (heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17
-	30949		USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:50
-	0	(after adj2 etching) with ((((cleaning ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj residue) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP))) with microwave) or (heating ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP) with microwave))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17
	3651	(plasma and etching and heating and (wafer or semiconductor)) and (after adj2 etching)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:51
-	17	(heating with microwave) with plasma adj (vessel or reactor or chamber)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 13:54
_	0	(heating with microwave) adj4 (plasma adj (vessel or reactor or chamber))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/08/17 13:54
-	0	(heating with microwave) adj7 (plasma adj (vessel or reactor or chamber))	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/08/17 13:54

-	17	((heating with microwave) with plasma	USPAT;	2004/08/17
		adj chamber) or ((heating with	US-PGPUB;	13:55
		microwave) with plasma adj (vessel or	EPO; JPO;	
		reactor or chamber))	IBM_TDB	
-	1	(after adj2 etching) with (heating adj4	USPAT;	2004/08/17
		microwave)	US-PGPUB;	14:14
			EPO; JPO;	
	54404		IBM_TDB	
_	71124	purging or evacuating	USPAT;	2004/08/17
			US-PGPUB;	14:14
			EPO; JPO;	
	71142	(numging on evacuating) on ((((a)coning	IBM_TDB	2004/00/17
_	71142	(purging or evacuating) or ((((cleaning	USPAT;	2004/08/17
,		ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or	US-PGPUB;	14:15
		((removing adj residue) ADJ5 (WAFER OR	EPO; JPO;	
		SEMICONDUCTOR OR CHIP)) or ((removing adj contaminants) ADJ5 (WAFER OR	IBM_TDB	
		SEMICONDUCTOR OR CHIP))) with microwave)		
		or (heating ADJ5 (WAFER OR SEMICONDUCTOR		
		OR CHIP) with microwave)) with (heating		
		adi4 microwave))		
1_	0	(purging or evacuating) and ((((cleaning	USPAT;	2004/08/17
		ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)) or	US-PGPUB;	14:15
		((removing adj residue) ADJ5 (WAFER OR	EPO; JPO;	14.15
		SEMICONDUCTOR OR CHIP)) or ((removing adj	IBM TDB	
		contaminants) ADJ5 (WAFER OR	1511_155	1
		SEMICONDUCTOR OR CHIP))) with microwave)		1
		or (heating ADJ5 (WAFER OR SEMICONDUCTOR		
		OR CHIP) with microwave)) with (heating		
		adj4 microwave))		
_	18		USPAT;	2004/08/17
i		OR CHIP)) or ((removing adj residue) ADJ5	US-PGPUB;	14:15
		(WAFER OR SEMICONDUCTOR OR CHIP)) or	EPO; JPO;	
		((removing adj contaminants) ADJ5 (WAFER	IBM TDB	
		OR SEMICONDUCTOR OR CHIP))) with	_	
	+	microwave) or (heating ADJ5 (WAFER OR		
		SEMICONDUCTOR OR CHIP) with microwave))		
		with (heating adj4 microwave)	ľ	
-	152	((plasma and etching and heating and	USPAT;	2004/08/17
		(wafer or semiconductor)) and	US-PGPUB;	14:24
		((((cleaning ADJ5 (WAFER OR SEMICONDUCTOR	EPO; JPO;	
		OR CHIP)) or ((removing adj residue) ADJ5	IBM_TDB	
		(WAFER OR SEMICONDUCTOR OR CHIP)) or		
		((removing adj contaminants) ADJ5 (WAFER		
		OR SEMICONDUCTOR OR CHIP))) with		
		microwave) or (heating ADJ5 (WAFER OR		
		SEMICONDUCTOR OR CHIP) with microwave))) or ((((cleaning ADJ5 (WAFER OR		
	1			
	1	SEMICONDUCTOR OR CHIP)) or ((removing adjresidue) ADJ5 (WAFER OR SEMICONDUCTOR OR		
		CHIP)) or ((removing adj contaminants)		
		ADJ5 (WAFER OR SEMICONDUCTOR OR CHIP)))		
	İ	with microwave) or (heating ADJ5 (WAFER		
		OR SEMICONDUCTOR OR CHIP) with		
		microwave))		
1	1	mrcrondvc//		I